

Shou Jinn Chang

List of Publications by Year in descending order

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327
papers

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330
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docs citations

330
times ranked

4831
citing authors

#	ARTICLE	IF	CITATIONS
1	The study of humidity sensor based on Li-doped ZnO nanorods by hydrothermal method. <i>Microsystem Technologies</i> , 2022, 28, 423-427.	1.2	4
2	Aluminum-doped zinc oxide nanorods and methyl alcohol gas sensor application. <i>Microsystem Technologies</i> , 2022, 28, 377-382.	1.2	6
3	Advanced Nanomaterials for Applications in Photonic and Sensor Devices. <i>Journal of Nanomaterials</i> , 2022, 2022, 1-2.	1.5	4
4	High Stability Flexible Deep-UV Detector Based on All-Oxide Heteroepitaxial Junction. <i>ACS Applied Electronic Materials</i> , 2022, 4, 3099-3106.	2.0	9
5	The Characteristics of Aluminum-Gallium-Zinc-Oxide Ultraviolet Phototransistors by Co-Sputtering Method. <i>Electronics (Switzerland)</i> , 2021, 10, 631.	1.8	2
6	Stability-Enhanced Resistive Random-Access Memory via Stacked In _x Ga _{1-x} O by the RF Sputtering Method. <i>ACS Omega</i> , 2021, 6, 10691-10697.	1.6	4
7	High Response of Ethanol Gas Sensor Based on NiO-Doped Apple Pectin by the Solution Process. <i>Coatings</i> , 2021, 11, 1073.	1.2	1
8	Performance Improvement of Co-Sputtering AlGaZnO Solar-Blind Photodetectors. <i>IEEE Sensors Journal</i> , 2021, 21, 18682-18687.	2.4	2
9	Indium Aluminum Zinc Oxide Phototransistor With HfO ₂ Dielectric Layer Through Atomic Layer Deposition. <i>IEEE Sensors Journal</i> , 2020, 20, 1838-1842.	2.4	3
10	Photoresponses of Zinc Tin Oxide Thin-Film Transistor. <i>Journal of Nanoscience and Nanotechnology</i> , 2020, 20, 1704-1708.	0.9	7
11	Voltage-Tunable UVC–UVB Dual-Band Metal–Semiconductor–Metal Photodetector Based on Ga ₂ O ₃ /MgZnO Heterostructure by RF Sputtering. <i>Coatings</i> , 2020, 10, 994.	1.2	6
12	Fabrication of Silicon Dioxide by Photo-Chemical Vapor Deposition to Decrease Detector Current of ZnO Ultraviolet Photodetectors. <i>ACS Omega</i> , 2020, 5, 27566-27571.	1.6	3
13	Investigation of Conductive Mechanism of Amorphous IGO Resistive Random-Access Memory with Different Top Electrode Metal. <i>Coatings</i> , 2020, 10, 504.	1.2	4
14	An Amorphous (Al _{0.12} Ga _{0.88}) ₂ O ₃ Deep Ultraviolet Photodetector. <i>IEEE Photonics Journal</i> , 2020, 12, 1-8.	1.0	2
15	Selected Papers from IEEE ICASI 2018. <i>Applied Sciences (Switzerland)</i> , 2020, 10, 964.	1.3	0
16	Polycrystalline In–Ga–O Thin-Film Transistors Coupled With a Nitrogen Doping Technique for High-Performance UV Detectors. <i>IEEE Transactions on Electron Devices</i> , 2020, 67, 140-145.	1.6	3
17	Investigation of nitrogen doping effects on light-induced oxygen vacancy ionization and oxygen desorption in c-IGO TFTs. <i>Materials Research Express</i> , 2019, 6, 106445.	0.8	3
18	Fast Detection and Flexible Microfluidic pH Sensors Based on Al-Doped ZnO Nanosheets with a Novel Morphology. <i>ACS Omega</i> , 2019, 4, 19847-19855.	1.6	27

#	ARTICLE	IF	CITATIONS
19	Design of Dual-Band Bandpass Filter With Simultaneous Narrow- and Wide-Bandwidth and a Wide Stopband. IEEE Access, 2019, 7, 147694-147703.	2.6	14
20	Ultraviolet/Visible Photodetectors Based on NiO/ZnO Nanowires Decorated with Pd Nanoparticles. ACS Applied Nano Materials, 2019, 2, 6343-6351.	2.4	36
21	Enhanced Detection of Ethanol in a Humid Ambient Using Al_2O_3 -Doped Cactus-Like ZnO Nanoflowers With Gold Nanoparticles. IEEE Transactions on Device and Materials Reliability, 2019, 19, 409-415.	1.5	4
22	Integration of bandgap-engineered double-stacked channel layers with nitrogen doping for high-performance InGaO TFTs. Applied Physics Letters, 2019, 114, .	1.5	20
23	Indium Aluminum Zinc Oxide Thin Film Transistor With Al_2O_3 Dielectric for UV Sensing. IEEE Photonics Technology Letters, 2019, 31, 1005-1008.	1.3	7
24	Indium Gallium Oxide Thin Film Transistor for Two-Stage UV Sensor Application. ECS Journal of Solid State Science and Technology, 2019, 8, Q3140-Q3143.	0.9	15
25	Stability Improvement of Nitrogen Doping on IGO TFTs under Positive Gate Bias Stress and Hysteresis Test. ECS Journal of Solid State Science and Technology, 2019, 8, Q3034-Q3040.	0.9	10
26	Bandgap Engineered Ultraviolet Photodetectors with Gallium-Zinc-Oxide via Co-Sputtering Method. ECS Journal of Solid State Science and Technology, 2018, 7, Q3083-Q3088.	0.9	6
27	Visible Illumination Enhanced Noenzymatic Glucose Photobiosensor Based on TiO_2 Nanorods Decorated With Au Nanoparticles. IEEE Transactions on Biomedical Engineering, 2018, 65, 2052-2057.	2.5	5
28	Through-silicon via submount for the CuO/Cu ₂ O nanostructured field emission display. RSC Advances, 2018, 8, 706-709.	1.7	3
29	High Density Novel Porous ZnO Nanosheets Based on a Microheater Chip for Ozone Sensors. IEEE Sensors Journal, 2018, 18, 5559-5565.	2.4	26
30	Amorphous Indium Titanium Zinc Oxide Thin Film Transistor and Impact of Gate Dielectrics on Its Photo-Electrical Properties. ECS Journal of Solid State Science and Technology, 2018, 7, Q3049-Q3053.	0.9	3
31	Photo-Electrical Properties of MgZnO Thin-Film Transistors With High- ϵ_r Dielectrics. IEEE Photonics Technology Letters, 2018, 30, 59-62.	1.3	17
32	Photoresponses of Gallium Zinc Tin Oxide Thin-Film Transistors Fabricated by Cosputtering Method. , 2018, 2, 1-4.		1
33	UV-Enhanced 2-D Nanostructured ZnO Field Emitter With Adsorbed Pt Nanoparticles. IEEE Electron Device Letters, 2018, 39, 1932-1935.	2.2	6
34	High Sensitivity of NO Gas Sensors Based on Novel Ag-Doped ZnO Nanoflowers Enhanced with a UV Light-Emitting Diode. ACS Omega, 2018, 3, 13798-13807.	1.6	92
35	Effects of Average Power-Handling Capability on DC-Sputtering Aluminum Nitride Thin Film on Ceramic Substrate. , 2018, , .		1
36	Effect of Oxygen Vacancy Ratio on a GaZTO Solar-Blind Photodetector. Coatings, 2018, 8, 293.	1.2	14

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37	Electrical Properties of Indium Aluminum Zinc Oxide Thin Film Transistors. Journal of Electronic Materials, 2018, 47, 6923-6928.	1.0	17
38	Highly stable ITO/Zn ₂ TiO ₄ /Pt resistive random access memory and its application in two-bit-per-cell. RSC Advances, 2018, 8, 17622-17628.	1.7	12
39	Bandgap-Engineered Zinc-Tin-Oxide Thin Films for Ultraviolet Sensors. Journal of Nanoscience and Nanotechnology, 2018, 18, 4930-4934.	0.9	3
40	Optical and photo-electrical properties of zinc tin oxide thin-film phototransistor. , 2018, , .		2
41	Effect of different partial pressure on Ga-doped ZnO UV photodetectors by RF sputtering. , 2018, , .		0
42	Introduction to a New Journal: Applied System Innovation. Applied System Innovation, 2018, 1, 1.	2.7	14
43	Design of Dual-Band Transparent Antenna by Using Nano-Structured Thin Film Coating Technology. , 2018, , .		2
44	Fabrication of Zinc Oxide-Based Thin-Film Transistors by Radio Frequency Sputtering for Ultraviolet Sensing Applications. Journal of Nanoscience and Nanotechnology, 2018, 18, 3518-3522.	0.9	5
45	A Bifacial SnO ₂ Thin-Film Ethanol Gas Sensor. IEEE Electron Device Letters, 2018, 39, 1223-1225.	2.2	14
46	Properties of Ga-Zn-O Ultraviolet Phototransistors Using Radio-Frequency Magnetron Co-Sputtering Method. Nanoscience and Nanotechnology Letters, 2018, 10, 396-402.	0.4	1
47	Tunable UV- and Visible-Light Photoresponse Based on p-ZnO Nanostructures/n-ZnO/Glass Peppered with Au Nanoparticles. ACS Applied Materials & Interfaces, 2017, 9, 14935-14944.	4.0	57
48	Thin-Film Transistors With Amorphous Indium-Gallium-Oxide Bilayer Channel. IEEE Electron Device Letters, 2017, 38, 572-575.	2.2	18
49	Nonenzymatic Glucose Sensor Based on Au/ZnO Core-Shell Nanostructures Decorated with Au Nanoparticles and Enhanced with Blue and Green Light. Journal of Physical Chemistry B, 2017, 121, 2931-2941.	1.2	27
50	A WO ₃ Nanoparticles NO Gas Sensor Prepared by Hot-Wire CVD. IEEE Electron Device Letters, 2017, 38, 266-269.	2.2	36
51	Performance improvement of highly mismatched GaSb layers on GaAs by interfacial-treatment-assisted chemical vapor deposition. Journal of Materials Science: Materials in Electronics, 2017, 28, 845-855.	1.1	0
52	Growth and characterization of high quality N-type GaSb/GaAs heterostructure by IMF growth mode using MOCVD for low power application. Applied Physics Letters, 2017, 111, 162108.	1.5	1
53	System setup consideration for range gated imaging. , 2017, , .		0
54	High Responsivity MgZnO Ultraviolet Thin-Film Phototransistor Developed Using Radio Frequency Sputtering. Materials, 2017, 10, 126.	1.3	23

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55	Oxygen Partial Pressure Impact on Characteristics of Indium Titanium Zinc Oxide Thin Film Transistor Fabricated via RF Sputtering. <i>Nanomaterials</i> , 2017, 7, 156.	1.9	15
56	The Effect of the Thickness and Oxygen Ratio Control of Radio-Frequency Magnetron Sputtering on MgZnO Thin-Film Transistors. <i>Journal of Nanoscience and Nanotechnology</i> , 2017, 17, 2037-2040.	0.9	1
57	Detection Method of Alcohol in Calf Serum with Zinc Oxide Nanowire Ethanol Sensor. <i>Journal of Nanoscience and Nanotechnology</i> , 2017, 17, 2104-2108.	0.9	0
58	High efficiency transparent digital television antenna based on nano-structured thin film coating technology. , 2017, , .		2
59	Ultimate Aims and Prospects of Inventions. <i>Inventions</i> , 2016, 1, 1-2.	1.3	9
60	Enhanced Photoluminescent Properties and Crystalline Morphology of LiBaPO ₄ :Tm ³⁺ Phosphor through Microwave Sintering Method. <i>Materials</i> , 2016, 9, 356.	1.3	7
61	Preparation of a Carbon Doped Tissue-Mimicking Material with High Dielectric Properties for Microwave Imaging Application. <i>Materials</i> , 2016, 9, 559.	1.3	7
62	Design of wideband bandpass filter using mode-exciting technology. <i>Microwave and Optical Technology Letters</i> , 2016, 58, 1507-1510.	0.9	2
63	Synthesis of In ₂ O ₃ Nanowires and Their Gas Sensing Properties. <i>IEEE Sensors Journal</i> , 2016, 16, 5850-5855.	2.4	8
64	Fabrication and characterization of GaN ultraviolet photodetector prepared by growing on geometrical patterned sapphire substrate. , 2016, , .		0
65	A three-dimensional ZnO nanowires photodetector. , 2016, , .		0
66	Electron field emitters made of 3-D CuO nanowires on flexible silicon substrate fabricated by heating Cu rods with through silicon via process. <i>RSC Advances</i> , 2016, 6, 47292-47297.	1.7	4
67	Design of a Compact Ultra-Wideband Bandpass Filter With an Extremely Broad Stopband Region. <i>IEEE Microwave and Wireless Components Letters</i> , 2016, 26, 392-394.	2.0	44
68	Effect of different alkali carbonate on the microstructure and photoluminescent properties of YInGe ₂ O ₇ :Eu ³⁺ phosphors. <i>Journal of Materials Science: Materials in Electronics</i> , 2016, 27, 2963-2967.	1.1	5
69	p-MOSFET and n-MOSFET prepared by ICP-assisted hot wire implantation doping technique. <i>IEEE Electron Device Letters</i> , 2016, , 1-1.	2.2	1
70	Transparent ZnO-nanowire-based device for UV light detection and ethanol gas sensing on c-Si solar cell. <i>RSC Advances</i> , 2016, 6, 11146-11150.	1.7	35
71	High Responsivity Mg _x Zn _{1-x} O Film UV Photodetector Grown by RF Sputtering. <i>IEEE Photonics Technology Letters</i> , 2015, 27, 978-981.	1.3	18
72	Assessment of dielectric properties for the microwave phantom production. , 2015, , .		0

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73	InGaN-based MQE LEDs with tunnel-junction-cascaded structure. , 2015, , .		0
74	GaN-based LEDs with flower shape ZnO nanorods by SILAR-based and hydrothermal methods. , 2015, , .		0
75	A compact low-pass filter with ultrabroad stopband characteristics. Microwave and Optical Technology Letters, 2015, 57, 2800-2803.	0.9	5
76	Applications of Advanced Nanomaterials to Microelectronic and Photonic Devices. Journal of Nanomaterials, 2015, 2015, 1-1.	1.5	2
77	Transmission Properties in Lossy Single-Negative Materials. IEEE Photonics Journal, 2015, 7, 1-8.	1.0	0
78	Amorphous Indium-Gallium-Oxide UV Photodetectors. IEEE Photonics Technology Letters, 2015, 27, 2083-2086.	1.3	41
79	An excellent encapsulation of silicone on an optimized-ZnO-nanowires anti-reflection layer for crystalline-Si photovoltaic devices. , 2015, , .		0
80	c-Si solar cells and Si n-MOSFETs prepared by ICP assisted hot wire implantation doping. RSC Advances, 2015, 5, 96547-96550.	1.7	1
81	GaN-Based High-Voltage Light-Emitting Diodes With SU-8 Passivation. Journal of Display Technology, 2015, 11, 374-377.	1.3	7
82	Bandgap-Engineered Indium-Gallium-Oxide Ultraviolet Phototransistors. IEEE Photonics Technology Letters, 2015, 27, 915-918.	1.3	41
83	Terahertz Negative Refraction in a High-Temperature Superconducting Material. IEEE Transactions on Terahertz Science and Technology, 2015, 5, 230-235.	2.0	2
84	GaN MSM UV Photodetector With Sputtered AlN Nucleation Layer. IEEE Sensors Journal, 2015, 15, 4743-4748.	2.4	37
85	Investigation of optical and electrical properties of GaN-based blue light-emitting diodes with various quantum well thicknesses. Journal of Photonics for Energy, 2015, 5, 057612.	0.8	6
86	Electron field emission enhancement of hybrid Cu/CuO nanowires fabricated by rapid thermal reduction of CuO nanowires. RSC Advances, 2015, 5, 54220-54224.	1.7	11
87	Conversion Efficiency Improvement of InGaN/GaN Multiple-Quantum-Well Solar Cells With Ex Situ AlN Nucleation Layer. IEEE Transactions on Electron Devices, 2015, 62, 1473-1477.	1.6	7
88	A Simple and Effective Method for Designing Frequency Adjustable Balun Diplexer With High Common-Mode Suppression. IEEE Microwave and Wireless Components Letters, 2015, 25, 433-435.	2.0	14
89	Effects of last barrier thickness on the hot-cold factor of GaN-based light-emitting diodes. Journal of Photonics for Energy, 2015, 5, 057602.	0.8	0
90	Effects of microcell layout on the performance of GaN-based high-voltage light-emitting diodes. Journal of Photonics for Energy, 2015, 5, 057605.	0.8	6

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91	Synthesis of CuInS ₂ quantum dots using polyetheramine as solvent. Nanoscale Research Letters, 2015, 10, 122.	3.1	16
92	GaN-Based Power Flip-Chip LEDs With SILAR and Hydrothermal ZnO Nanorods. IEEE Journal of Selected Topics in Quantum Electronics, 2015, 21, 431-435.	1.9	3
93	Two-bit-per-cell resistive switching memory device with a Ti/MgZnO/Pt structure. RSC Advances, 2015, 5, 88166-88170.	1.7	11
94	Effects of humidity and ultraviolet characteristics on \hat{I}^2 -Ga ₂ O ₃ nanowire sensor. RSC Advances, 2015, 5, 84776-84781.	1.7	18
95	AlGaInP-based LEDs with ZnO nanostructures by successive ionic layer adsorption and reaction and hydrothermal methods. , 2015, , .		0
96	Effect of Solvent Chelating on Crystal Growth Mechanism of CZTSe Nanoink in Polyetheramine. IEEE Nanotechnology Magazine, 2015, 14, 896-903.	1.1	1
97	Enhanced field emission properties based on In ⁺ In ₂ O ₃ composite nanopagodas. RSC Advances, 2015, 5, 5192-5196.	1.7	3
98	GaN-Based LEDs With Hot/Cold Factor Improved by the Electron Blocking Layer. Journal of Display Technology, 2014, 10, 1078-1082.	1.3	5
99	Frequency Response of a Ferroelectric Material in Double-Negative Region. IEEE Photonics Journal, 2014, 6, 1-11.	1.0	0
100	Integration of a-IGZO Thin-Film Transistor and Crystalline-Si Interdigitated Back Contact Photovoltaic Cell With 3D Stacking Structure as Self-Powered Solar Switch. IEEE Electron Device Letters, 2014, 35, 1040-1042.	2.2	3
101	Optimization of the dye-sensitized solar cell performance by mechanical compression. Nanoscale Research Letters, 2014, 9, 523.	3.1	24
102	A triband bandpass filter with low loss and high band selectivity using the split ⁺ asymmetric stepped impedance resonators. Microwave and Optical Technology Letters, 2014, 56, 1427-1430.	0.9	6
103	Characteristics of TiO ₂ /metal-semiconductor-metal photodetectors with O ₂ /plasma treatment. , 2014, , .		1
104	Investigation of zinc-tin-oxide thin-film transistors with varying SnO ₂ contents. Electronic Materials Letters, 2014, 10, 89-94.	1.0	8
105	UV Enhanced Field Emission Performance of Mg-Doped ZnO Nanorods. IEEE Transactions on Electron Devices, 2014, 61, 1541-1545.	1.6	26
106	A high selectivity and wide stopband UWB bandpass filter using asymmetric SIRs with split ⁺ . Microwave and Optical Technology Letters, 2014, 56, 1353-1356.	0.9	1
107	ZnO nanowires modified with Au nanoparticles for nonenzymatic amperometric sensing of glucose. Applied Physics Letters, 2014, 104, .	1.5	28
108	GaN-Based Light-Emitting-Diode With a p-InGaN Layer. Journal of Display Technology, 2014, 10, 204-207.	1.3	0

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109	Visible-Blind Photodetectors With Mg-Doped ZnO Nanorods. IEEE Photonics Technology Letters, 2014, 26, 645-648.	1.3	34
110	Enhanced Field Emission of TiO_2 Nanowires With UV Illumination. IEEE Electron Device Letters, 2014, 35, 123-125.	2.2	9
111	GaN-Based LEDs With Rough Surface and Selective KOH Etching. Journal of Display Technology, 2014, 10, 27-32.	1.3	8
112	Two-dimensional ZnO nanowalls for gas sensor and photoelectrochemical applications. Electronic Materials Letters, 2014, 10, 693-697.	1.0	14
113	Effect of V/III ratios on surface morphology in a GaSb thin film grown on GaAs substrate by MOCVD. , 2014, , .		0
114	GaN-Based Light-Emitting Diodes With Staircase Electron Injector Structure. Journal of Display Technology, 2014, 10, 162-166.	1.3	3
115	Amorphous InGaZnO Ultraviolet Phototransistors With a Thin Ga_2O_3 Layer. IEEE Journal of Selected Topics in Quantum Electronics, 2014, 20, 125-129.	1.9	14
116	Failure Mechanism for GaN-Based High-Voltage Light-Emitting Diodes. IEEE Photonics Technology Letters, 2014, 26, 1073-1076.	1.3	9
117	ZnO Branched Nanowires and the p-CuO/n-ZnO Heterojunction Nanostructured Photodetector. IEEE Nanotechnology Magazine, 2013, 12, 263-269.	1.1	62
118	Diluted Magnetic Nanosemiconductor: Fe-Doped ZnO Vertically Aligned Nanorod Arrays Grown by Hydrothermal Synthesis. IEEE Nanotechnology Magazine, 2013, 12, 649-655.	1.1	7
119	Carbon Nanotubes With Adsorbed Au for Sensing Gas. IEEE Sensors Journal, 2013, 13, 2423-2427.	2.4	36
120	Noise Properties of ZnO Nanowalls Deposited Using Rapid Thermal Evaporation Technology. IEEE Photonics Technology Letters, 2013, 25, 213-216.	1.3	7
121	Investigating the Effect of Piezoelectric Polarization on GaN-Based LEDs With Different Quantum Barrier Thickness. Journal of Display Technology, 2013, 9, 206-211.	1.3	14
122	Ga_2O_3 /GaN-Based Metal-Semiconductor-Metal Photodetectors Covered With Au Nanoparticles. IEEE Photonics Technology Letters, 2013, 25, 1809-1811.	1.3	18
123	Ga_2O_3 Nanowire Photodetector Prepared on SiO_2/Si Template. IEEE Sensors Journal, 2013, 13, 2368-2373.	2.4	40
124	Low-Frequency Noise Characteristics of In-Doped ZnO Ultraviolet Photodetectors. IEEE Photonics Technology Letters, 2013, 25, 2043-2046.	1.3	24
125	GaN-Based LEDs With an HT-AlN Nucleation Layer Prepared on Patterned Sapphire Substrate. IEEE Photonics Technology Letters, 2013, 25, 88-90.	1.3	5
126	Electron-Field-Emission Properties of Gallium Compound by Ammonification of Ga_2O_3 Nanowires. IEEE Nanotechnology Magazine, 2013, 12, 692-695.	1.1	1

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127	$\text{AlGaIn}/\text{GaInN}$ Heterostructure Ultraviolet Three-Band Photodetector. IEEE Sensors Journal, 2013, 13, 3462-3467.	2.4	32
128	Effect of surface modification by self-assembled monolayer on the ZnO film ultraviolet sensor. Applied Physics Letters, 2013, 103, 022101.	1.5	6
129	InGaIn/GaIn Multi-Quantum-Well Metal-Semiconductor-Metal Photodetectors With Beta- AlGaIn Cap Layers. IEEE Sensors Journal, 2013, 13, 1187-1191.	2.4	16
130	$\text{AlGaIn}/\text{GaInN}$ Nanowires-Based Humidity Sensors Prepared on GaIn/Sapphire Substrate. IEEE Sensors Journal, 2013, 13, 4891-4896.	2.4	11
131	GaIn-Based Light-Emitting Diodes With Step Graded-Refractive Index ZnO/SiO_2 Micropillar Array. Journal of Display Technology, 2013, 9, 353-358.	1.3	1
132	Field-Emission and Photoelectrical Characteristics of GaIn/ZnO Nanorods Photodetector. IEEE Transactions on Electron Devices, 2013, 60, 1905-1910.	1.6	39
133	Numerical Simulation of GaIn-Based LEDs With Chirped Multi-Quantum Barrier Structure. IEEE Journal of Quantum Electronics, 2013, 49, 436-442.	1.0	11
134	UV Enhanced Field Emission for ZnO -GaIn Nanowires. IEEE Electron Device Letters, 2013, 34, 701-703.	2.2	3
135	Photoelectrical and Low-Frequency Noise Characteristics of ZnO Nanorod Photodetectors Prepared on Flexible Substrate. IEEE Transactions on Electron Devices, 2013, 60, 229-234.	1.6	23
136	Dislocation reduction through nucleation and growth selectivity of metal-organic chemical vapor deposition GaIn. Journal of Applied Physics, 2013, 113, 144908.	1.1	10
137	Improved Field Emission Properties of Ag-Decorated Multi-Walled Carbon Nanotubes. IEEE Photonics Technology Letters, 2013, 25, 1017-1019.	1.3	18
138	InGaP/GaAs/Ge triple-junction solar cells with ZnO nanowires. Progress in Photovoltaics: Research and Applications, 2013, 21, 1645-1652.	4.4	12
139	Improved efficiency of p-type quasi-mono silicon blanket emitter solar cell by ion implantation and backside rounding. Materials Science-Poland, 2013, 31, 516-524.	0.4	0
140	Noise Properties of Fe-ZnO Nanorod Ultraviolet Photodetectors. IEEE Photonics Technology Letters, 2013, 25, 2089-2092.	1.3	16
141	Improved Carrier Distributions by Varying Barrier Thickness for InGaIn/GaIn LEDs. Journal of Display Technology, 2013, 9, 239-243.	1.3	13
142	Effects of Initial GaIn Growth Mode on Patterned Sapphire on the Opto-Electrical Characteristics of GaIn-Based Light-Emitting Diodes. Journal of Display Technology, 2013, 9, 292-296.	1.3	7
143	Amorphous InGaZnO ultraviolet phototransistors with double-stack Ga ₂ O ₃ /SiO ₂ dielectric. Applied Physics Letters, 2013, 102, .	1.5	54
144	GaIn-Based Light-Emitting Diodes on Electrochemically Etched Al_2O_3 -GaIn Template. IEEE Photonics Technology Letters, 2013, 25, 1531-1534.	1.3	5

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145	Synchrotron radiation based cross-sectional scanning photoelectron microscopy and spectroscopy of n-ZnO:Al/p-GaN:Mg heterojunction. Applied Physics Letters, 2013, 102, .	1.5	6
146	UV Enhanced Indium-Doped ZnO Nanorod Field Emitter. IEEE Transactions on Electron Devices, 2013, 60, 3901-3906.	1.6	12
147	GaN-Based Ultraviolet Light Emitting Diodes With Ex Situ Sputtered AlN Nucleation Layer. Journal of Display Technology, 2013, 9, 895-899.	1.3	16
148	GaN Nanowire Field Emitters With the Adsorption of Au Nanoparticles. IEEE Electron Device Letters, 2013, 34, 553-555.	2.2	7
149	AlGaInP-Based LEDs With AuBe-Diffused AZO/GaP Current Spreading Layer. IEEE Journal of Quantum Electronics, 2013, 49, 846-851.	1.0	9
150	Surface plasmon-enhanced gas sensing in single gold-peapodded silica nanowires. NPG Asia Materials, 2013, 5, e49-e49.	3.8	19
151	Influence of Weight Ratio of Poly(4-vinylphenol) Insulator on Electronic Properties of InGaZnO Thin-Film Transistor. Journal of Nanomaterials, 2012, 2012, 1-7.	1.5	10
152	High responsivity of amorphous indium gallium zinc oxide phototransistor with Ta2O5 gate dielectric. Applied Physics Letters, 2012, 101, .	1.5	67
153	Effect of Varied Undoped GaN Thickness on ESD and Optical Properties of GaN-Based LEDs. IEEE Photonics Technology Letters, 2012, 24, 800-802.	1.3	5
154	Impact of oxygen annealing on high-k gate stack defects characterized by random telegraph noise. Applied Physics Letters, 2012, 101, 122105.	1.5	10
155	A Flexible ZnO Nanowire-Based Humidity Sensor. IEEE Nanotechnology Magazine, 2012, 11, 520-525.	1.1	24
156	GaN-Based Light-Emitting Diode With Sputtered AlN Nucleation Layer. IEEE Photonics Technology Letters, 2012, 24, 294-296.	1.3	49
157	Characteristics of GaN/InGaN Double-Heterostructure Photovoltaic Cells. International Journal of Photoenergy, 2012, 2012, 1-5.	1.4	4
158	A Visible-Blind TiO2Nanowire Photodetector. Journal of the Electrochemical Society, 2012, 159, J132-J135.	1.3	41
159	Characteristics of Thin-Film-Transistors Based on Zn–In–Sn–O Thin Films Prepared by Co-Sputtering System. Materials Transactions, 2012, 53, 571-574.	0.4	1
160	Microstructural Characteristics of InGaZnO Thin Film Using an Electrical Current Method. Materials Transactions, 2012, 53, 733-738.	0.4	3
161	The Effects of Crystallization on Mechanical Mechanism and Residual Stress of Sputtered Ag Thin Films. Materials Transactions, 2012, 53, 2049-2055.	0.4	3
162	GaN-Based LEDs with a Mirror Structure and an Insulating Layer. , 2012, , .		0

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163	Enhanced Current Spreading for GaN-Based Side-View LEDs by Adding an Metallic Stripe Across the Long Side of the Chip. IEEE Photonics Technology Letters, 2012, 24, 1412-1414.	1.3	4
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